Revision. 3

MOS FET

SK8603150L

### **Panasonic**

### SK8603150L

#### Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

#### ■ Features

- Low Drain-source On-state Resistance : RDS(on) typ = 2.5 m $\Omega$  (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : 15

Established: 2012-09-19

: 2013-05-31

Revised

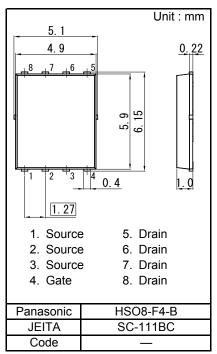
#### ■ Packaging

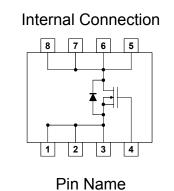
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter			Symbol	Rating		Unit	
Drain to Source Voltage			VDS	30		V	
Gate to Source Voltage			VGS	±20	)	V	
Drain Current	Ta = 25 °C, t = 10 s *1			40			
	Ta = 25 °C, DC *1		ID	26		Α	
	Tc = 25 °C			89		] ^	
	Pulsed	d, Tch < 150 °C <sup>*2</sup>		120	)		
Total Power Ta = 25		Ta = 25 °C, DC *1	PD	2.9	W		
Dissipation		Tc = 25 °C	FD	34			
Thermal Resistance		Channel to Ambient	Rth(ch-a)	42		°C / W	
memai Resisi	ance	Channel to Case	Rth(ch-c)	· ·		-0 / ٧٧	
Channel Temperature			Tch	150			
Operating ambient temperature			Topr	-40 to	+85	°C	
Storage Temperature Range		Tstg	-55 to	+150			
Avalanche Current (Single pulse) *3			IAR	20		Α	
Avalanche Energy (Single pulse) *3			EAR	46		mJ	

- Note \*1 Device mounted on a glass-epoxy board in Figure 1
  - \*2 Pulse test: Ensure that the channel temperature does not exceed 150 °C
  - \*3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25  $^{\circ}$ C (initial)





- Source
   Source
   Drain
   Drain
- 3. Source4. Gate7. Drain8. Drain



Figure 1 FR4 Glass-Epoxy Board 25.4 mm × 25.4 mm × 0.8 mm

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#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

#### Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = $\pm 16$ V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage		ID = 4.38 mA, VDS = 10 V	1.3		3	V
Drain-source On-state Resistance		ID = 20 A, VGS = 10 V		1.9	2.5	mΩ
Diani-source On-sidle Nesistance	RDS(on)2	ID = 20 A, VGS = 4.5 V		2.5	3.5	

#### **Dynamic Characteristics**

Dynamic characteriotics						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V		3 700	5 180	
Output Capacitance	Coss	f = 1 MHz		430	602	pF
Reverse Transfer Capacitance	Crss	1 = 1 MH2		310	496	
Turn-on Delay Time *1	td(on)	VDD = 15 V, VGS = 0 to 10 V		13		no
Rise Time *1	tr	ID = 20 A		14		ns
Turn-off Delay Time *1	td(off)	VDD = 15 V, VGS = 10 to 0 V		64		no
Fall Time *1	tf	ID = 20 A		9		ns
Total Gate Charge	Qg	VDD = 15 V VCS = 0 to 4 5 V		28		
Gate to Source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V ID = 20 A		9		nC
Gate to Drain Charge	Qgd	1D - 20 A		10		
Gate resistance	rg	f = 5 MHz		0.8	3	Ω

#### **Body Diode Characteristic**

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 20 A, VGS = 0 V		0.9	1.2	V

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

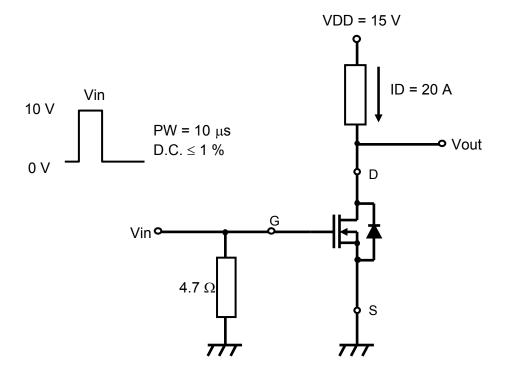
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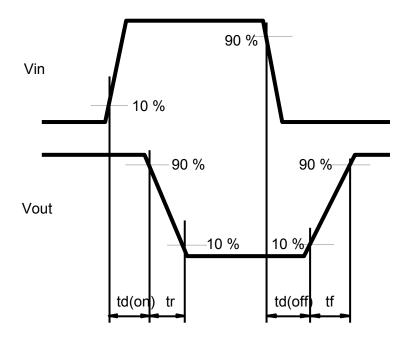
<sup>2. \*1</sup> Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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\*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time





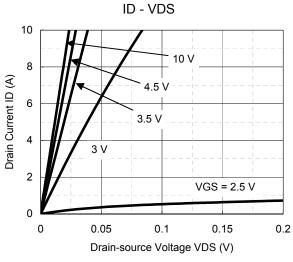
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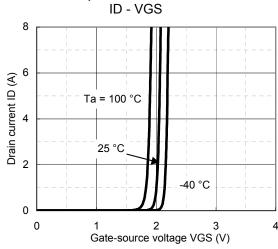
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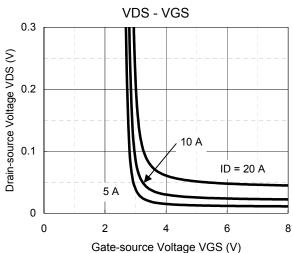
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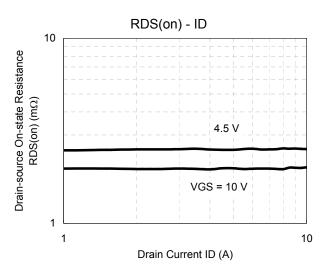
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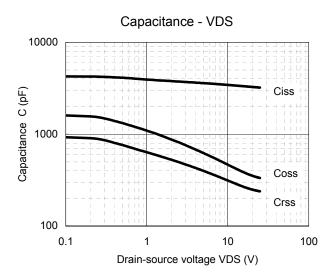


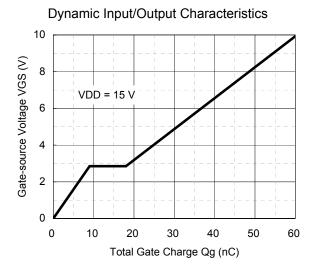








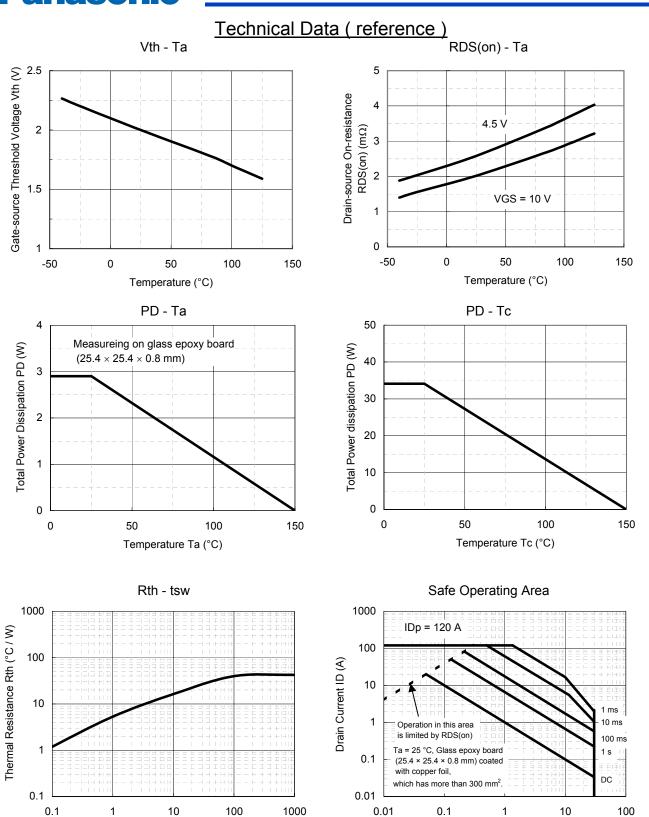




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Drain-source Voltage VDS (V)

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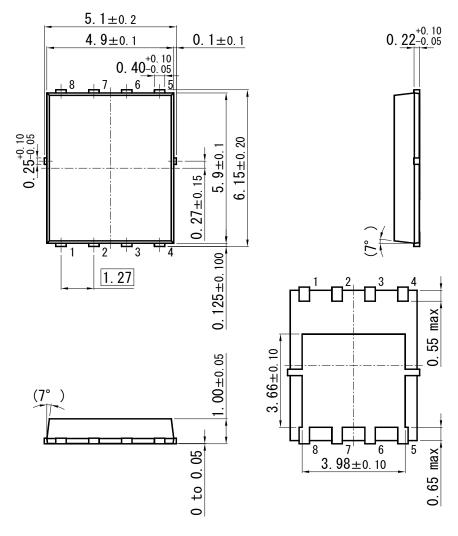
Pulse Width tsw (s)

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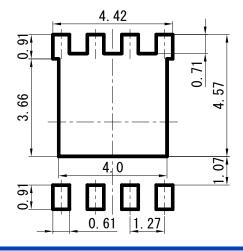
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HSO8-F4-B



■ Land Pattern (Reference) (Unit : mm)



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